- **Trimmed Offset Voltage:** TLC27M9 . . . 900 μ V Max at $T_{\Delta} = 25^{\circ}$ C, $V_{DD} = 5 V$
- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over **Specified Temperature Range:**

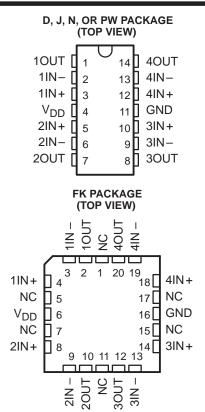
 0° C to 70° C . . . 3 V to 16 V -40°C to 85°C . . . 4 V to 16 V -55°C to 125°C . . . 4 V to 16 V

- **Single-Supply Operation**
- **Common-Mode Input Voltage Range** Extends Below the Negative Rail (C-Suffix, **I-Suffix Types)**
- Low Noise . . . Typically 32 nV/√Hz at f = 1 kHz
- Low Power . . . Typically 2.1 mW at $T_A = 25^{\circ}C, V_{DD} = 5 V$
- **Output Voltage Range Includes Negative**
- High Input Impedance . . . $10^{12} \Omega$ Typ
- **ESD-Protection Circuitry**
- **Small-Outline Package Option Also** Available in Tape and Reel
- **Designed-In Latch-Up Immunity**

description

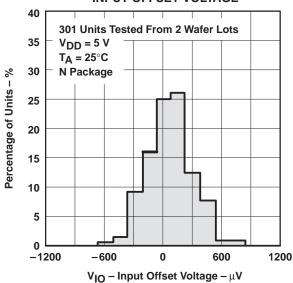
The TLC27M4 and TLC27M9 quad operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, low noise, and speeds comparable to that of general-purpose bipolar devices. These devices use Texas Instruments silicon-gate LinCMOS™ technology, provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, make these cost-effective devices ideal for applications that have previously been reserved for general-purpose bipolar products, but with only a fraction of the power consumption.



NC - No internal connection

DISTRIBUTION OF TLC27M9 INPUT OFFSET VOLTAGE





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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description (continued)

Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27M4 (10 mV) to the high-precision TLC27M9 (900 μV). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

In general, many features associated with bipolar technology are available on LinCMOS™ operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27M4 and TLC27M9. The devices also exhibit low voltage single-supply operation, and low power consumption, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

The device inputs and outputs are designed to withstand -100-mA surge currents without sustaining latch-up.

The TLC27M4 and TLC27M9 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015; however, care should be exercised in handling these devices, as exposure to ESD may result in the degradation of the device parametric performance.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to 85°C. The M-suffix devices are characterized for operation over the full military temperature range of -55°C to 125°C.

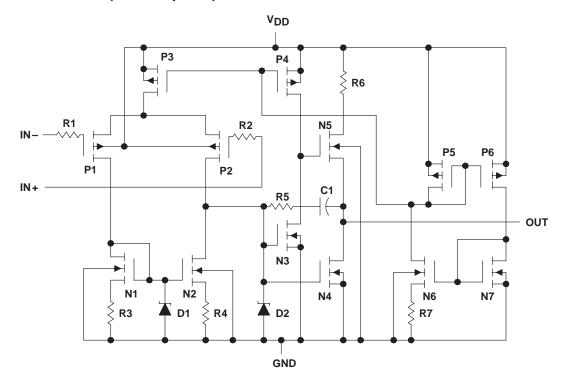
AVAILABLE OPTIONS

				PACKAGE			CHIP
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	FORM (Y)
	900 μV	TLC27M9CD	_	_	TLC27M9CN	_	_
0°C to 70°C	2 mV	TLC27M4BCD	_	_	TLC27M4BCN	_	_
0 0 10 70 0	5 mV	TLC27M4ACD	_	_	TLC27M4ACN	_	_
	10 mV	TLC27M4CD	_	_	TLC27M4CN	TLC27M4CPW	TLC27M4Y
	900 μV	TLC27M9ID	_	_	TLC27M9IN	_	_
-40°C to 85°C	2 mV	TLC27M4BID	_	_	TLC27M4BIN	_	_
-40 C to 65 C	5 mV	TLC27M4AID	_	_	TLC27M4AIN	_	_
	10 mV	TLC27M4ID	_	_	TLC27M4IN	TLC27M41PW	_
-55°C to 125°C	900 μV	TLC27M9MD	TLC27M9MFK	TLC27M9MJ	TLC27M9MN	_	_
-55 C to 125 C	10 mV	TLC27M4MD	TLC27M4MFK	TLC27M4MJ	TLC27M4MN	_	_

The D and PW package is available taped and reeled. Add R suffix to the device type (e.g., TLC279CDR).



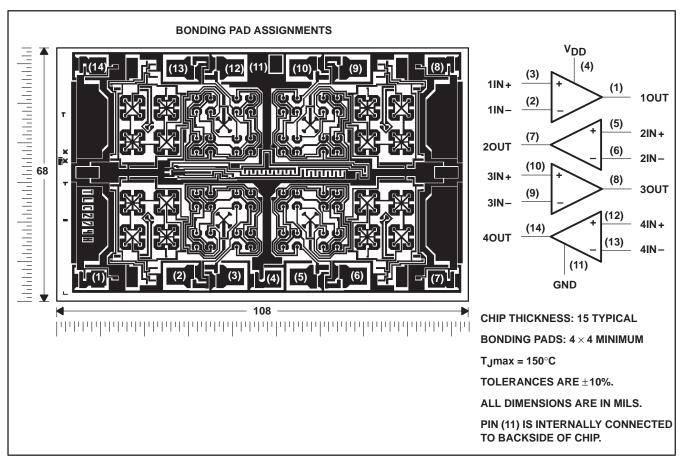
equivalent schematic (each amplifier)



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TLC27M4Y chip information

This chip, when properly assembled, displays characteristics similar to the TLC27M4C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	
Differential input voltage, V _{ID} (see Note 2)	±V _{DD}
Input voltage range, V _I (any input)	0.3 V to V _{DD}
Input current, I _I	±5 mA
Output current, I _O (each output)	±30 mA
Total current into V _{DD}	45 mA
Total current out of GND	45 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	unlimited
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature, T _A : C suffix	0°C to 70°C
I suffix	–40°C to 85°C
M suffix	–55°C to 125°C
Storage temperature range	–65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, N, or PW	package 260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: J package .	300°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	_
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
N	1575 mW	12.6 mW/°C	1008 mW	819 mW	_
PW	700 mW	5.6 mW/°C	448 mW	_	_

recommended operating conditions

		C SU	FFIX	I SUF	FIX	M SU	FFIX	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{DD}		3	16	4	16	4	16	V
Common mode input voltage V/o	V _{DD} = 5 V	-0.2	3.5	-0.2	3.5	0	3.5	V
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	V
Operating free-air temperature, TA		0	70	-40	85	-55	125	°C



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST COND	DITIONS	T _A †	TL TL	.C27M4 .C27M4 .C27M4 .C27M9	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27M4C	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		TLC27W4C	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	mV
		TLC27M4AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	IIIV
VIO	Input offset voltage	TEGZTWI4AC	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	
1 10	input onset voltage	TLC274BC	$V_0 = 1.4 V,$	$V_{IC} = 0$,	25°C		250	2000	
		12027480	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			3000	μV
		TLC279C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		210	900	μν
		1202730	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			1500	
ανιο	Average temperature coefficion offset voltage	ent of input			25°C to 70°C		1.7		μV/°C
1	Input offeet ourrent (see Note	. 4)	V _O = 2.5 V,	V:= - 2 5 V	25°C		0.1		
lio	Input offset current (see Note	÷ 4)	VO = 2.5 V,	$V_{IC} = 2.5 V$	70°C		7	300	pА
1.5	Input bias current (see Note 4)		Va - 25 V	V:= - 2 5 V	25°C		0.6		
IB	input bias current (see Note	4)	V _O = 2.5 V,	V _{IC} = 2.5 V	70°C		40	600	pА
						-0.2	-0.3		
					25°C	to 4	to 4.2		V
VICR	Common-mode input voltage (see Note 5)	range				-0.2	4.2		
					Full range	to 3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	0°C	3	3.9		V
					70°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	25	170		
A _{VD}	Large-signal differential voltage amplification		$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	0°C	15	200		V/mV
	voltage amplification				70°C	15	140		
					25°C	65	91		
CMRR	Common-mode rejection rati	0	V _{IC} = V _{ICR} min		0°C	60	91		dB
					70°C	60	92		
					25°C	70	93		
ksvr	Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	92		dB	
	יטט יטע /				70°C	60	94		
			V 0.5.V		25°C		420	1120	
IDD	Supply current (four amplifier	rs)	V _O = 2.5 V, No load	$V_{IC} = 2.5 V,$	0°C		500	1280	μΑ
	nge is 0°C to 70°C				70°C		340	880	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	Τ _Α †	TL TL	.C27M40 .C27M4/ .C27M41 .C27M90	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27M4C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		1.1	10	
		TEOZYWITO	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			12	mV
		TLC27M4AC	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		0.9	5	1 v
VIO	Input offset voltage	120271111110	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			6.5	
1,10	mpat oncot voltago	TLC27M4BC	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		260	2000	
		12027111130	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			3000	μV
		TLC27M9C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		220	1200	μν
		1202711100	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			1900	
ανιο	Average temperature coeffi offset voltage	cient of input			25°C to 70°C		2.1		μV/°C
l. a	Input offeet ourrent (see No	to 4)	V = - 5 V	V _{IC} = 5 V	25°C		0.1		nΛ
lιο	Input offset current (see No	ite 4)	$V_O = 5 V$,	AIC = 2A	70°C		7	300	pΑ
1	Innut bigg gurrant (age Not	. 4)	Va EV	V	25°C		0.7		~ Λ
ΙΒ	Input bias current (see Note	÷ 4)	V _O = 5 V,	$V_{IC} = 5 V$	70°C		50	600	pΑ
						-0.2	-0.3		
					25°C	to 9	to 9.2		V
VICR	Common-mode input voltage (see Note 5)	ge range			Full range	-0.2 to 8.5			V
					25°C	8	8.7		
∨он	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	0°C	7.8	8.7		V
					70°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	25	275		
A _{VD}	Large-signal differential voltage amplification		$V_0 = 1 \text{ V to 6 V},$	$R_L = 100 \text{ k}\Omega$	0°C	15	320		V/mV
	voltago amplinoation				70°C	15	230		
					25°C	65	94		
CMRR	Common-mode rejection ra	tio	V _{IC} = V _{ICR} min		0°C	60	94		dB
					70°C	60	94		
	O mark a salta and a	•_			25°C	70	93		
ksvr	Supply-voltage rejection ratio $(\Delta V_{DD}/\Delta V_{IO})$	IIO .	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	92		dB
	יטט				70°C	60	94		
					25°C		570	1200	
I _{DD}	Supply current (four amplifi	ers)	V _O = 5 V, No load	$V_{IC} = 5 V$,	0°C		690	1600	μΑ
					70°C		440	1120	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TL TL	.C27M4 .C27M4 .C27M4 .C27M9	AI BI	UNIT
		_				MIN	TYP	MAX	
		TLC27M4I	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		1.1	10	
		TLOZIWIHI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M4AI	$V_0 = 1.4 V$	$V_{IC} = 0$,	25°C		0.9	5	
VIO	Input offset voltage	TEO27WH7W	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			6.5	
۷۱٥	mpat onset voltage	TLC27M4BI	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		250	2000	
		TLOZ/IVI4DI	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			3000	μV
		TLC27M9I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		210	900	μν
		TEGETWIST	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			2000	
αΛΙΟ	Average temperature coeffic offset voltage	ient of input			25°C to 85°C		1.7		μV/°C
l	lanut effect ourrent (e.e. Net	- 4\	V- 25V	V 25V	25°C		0.1		Λ
lo	Input offset current (see Note	e 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	85°C		24	1000	pΑ
1	lanut hina aumant (ann Nata	4)	V- 05V	V:- 0.5.V	25°C		0.6		A
IB	Input bias current (see Note	4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$	85°C		200	2000	pΑ
						-0.2	-0.3		
					25°C	to	to		V
VICR	Common-mode input voltage	erange				4	4.2		
1011	(see Note 5)				Full range	-0.2 to			V
					Full rarige	3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltage		V _{ID} = 100 mV,	$R_I = 100 \text{ k}\Omega$	-40°C	3	3.9		V
011				_	85°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
02	, ,			02	85°C		0	50	
					25°C	25	170		
A_{VD}	Large-signal differential		$V_{O} = 0.25 \text{ V to 2 V},$	$R_I = 100 \text{ k}\Omega$	-40°C	15	270		V/mV
,,,	voltage amplification			_	85°C	15	130		
					25°C	65	91		
CMRR	Common-mode rejection rati	0	V _{IC} = V _{ICR} min		-40°C	60	90		dB
	•		30 .511		85°C	60	90		
					25°C	70	93		
ksvr	Supply-voltage rejection ratio)	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	-40°C	60	91		dB
	$(\Delta V_{DD}/\Delta V_{IO})$			-	85°C	60	94		
					25°C		420	1120	
I_{DD}	Supply current (four amplifie	rs)	$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 V,$	-40°C		630	1600	μΑ
		-	No load		85°C		320	800	

[†] Full range is –40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	Τ _Α †	TL TL	.C27M4I .C27M4I .C27M4I .C27M9I	AI BI	UNIT
						MIN	TYP	MAX	
		TLC27M4I	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		TLG27W4	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M4AI	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.9	5	IIIV
VIO	Input offset voltage	TEOZYWAAI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			7	
100	input onset voltage	TLC27M4BI	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		260	2000	
		TEG27W4BI	$R_S = 50 \Omega$,	R _L = 100 kΩ	Full range			3500	μV
		TLC27M9I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		220	1200	μν
		TEOZTWIST	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			2900	
ανιο	Average temperature coeffice offset voltage	cient of input			25°C to 85°C		2.1		μV/°C
1	Input offset ourrent (see No	·	V = - 5 V	V:= - 5 V	25°C		0.1		nΛ
lio	Input offset current (see No	e 4)	$V_O = 5 V$	$V_{IC} = 5 V$	85°C		26	1000	pΑ
1	Innut biog gurrent (age Note	4)	V- 5 V	V	25°C		0.7		π Λ
IB	Input bias current (see Note	4)	V _O = 5 V,	$V_{IC} = 5 V$	85°C		220	2000	pА
						-0.2	-0.3		
					25°C	to	to		V
VICR	Common-mode input voltage range (see Note 5)					9	9.2		
	voltage range (see Note 5)				Full range	-0.2 to			V
					l an range	8.5			ľ
					25°C	8	8.7		
VOH	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	-40°C	7.8	8.7		V
					85°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	25	275		
A _{VD}	Large-signal differential voltage amplification		$V_0 = 1 \text{ V to 6 V},$	$R_L = 100 \text{ k}\Omega$	−40°C	15	390		V/mV
					85°C	15	220		
					25°C	65	94		
CMRR	Common-mode rejection ra	io	V _{IC} = V _{ICR} min		−40°C	60	93		dB
					85°C	60	94		
	Cupply voltogs seisstics set				25°C	70	93		
ksvr	Supply-voltage rejection ration (ΔV _{DD} /ΔV _{IO})	U	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_O = 1.4 V$	-40°C	60	91		dB
	יטטי– יוטטי				85°C	60	94		
			V = - F V	V F.V	25°C		570	1200	
I_{DD}	Supply current (four amplifie	ers)	$V_O = 5 V$, No load	$V_{IC} = 5 V$,	−40°C		900	1800	μΑ
			1.0.000		85°C		410	1040	

[†] Full range is –40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †		.C27M4N .C27M9N		UNIT
						MIN	TYP	MAX	
		TI 0071444	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	\/
. ,	land offeringly	TLC27M4M	$R_S = 50 \Omega$	$R_L = 100 \text{ k}\Omega$	Full range			12	mV
VIO	Input offset voltage	TI CO7N40N4	V _O = 1.4 V,	V _{IC} = 0,	25°C		210	900	\/
		TLC27M9M	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3750	μV
ανιο	Average temperature coefficie offset voltage	nt of input			25°C to 125°C		1.7		μV/°C
	land offert comment (as a Nata	4)	V 05V	V 0.5.V	25°C		0.1		pА
10	Input offset current (see Note	4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	125°C		1.4	15	nA
1	lanut hina aumant (ann Nata 4	`	V- 05V	V:- 0.5.V	25°C		0.6		рΑ
ΙΒ	Input bias current (see Note 4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$	125°C		9	35	nA
\/	Common-mode input voltage	range			25°C	0 to 4	-0.3 to 4.2		٧
VICR	(see Note 5)				Full range	0 to 3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	−55°C	3	3.9		V
					125°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
	Large-signal differential				25°C	25	170		
A_{VD}	voltage amplification		$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	−55°C	15	290		V/mV
	- Tonago ampilioalion				125°C	15	120		
					25°C	65	91		
CMRR	Common-mode rejection ratio		VIC = VICRmin		−55°C	60	89		dB
					125°C	60	91		
	Cumply voltage rejection ratio				25°C	70	93		
ksvr	Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})		$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	−55°C	60	91		dB
					125°C	60	94		
		<u> </u>	V _O = 2.5 V,	V _{IC} = 2.5 V,	25°C		420	1120	
IDD	Supply current (four amplifier	s)	VO = 2.5 V, No load	VIC = 2.5 V,	−55°C		680	1760	μΑ
Ļ	and in FEOC to 1250C				125°C		280	720	

[†] Full range is -55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CO	NDITIONS	T _A †		.C27M4I .C27M9I		UNIT
						MIN	TYP	MAX	
		TLC27M4M	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	mV
V	Input offset voltage	1 LG27 IVI4IVI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	IIIV
VIO	input onset voitage	TLC27M9M	V _O = 1.4 V,	V _{IC} = 0,	25°C		220	1200	μV
		TLG27 IVI9IVI	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			4300	μν
ανιο	Average temperature coeffi offset voltage	cient of input			25°C to 125°C		2.1		μV/°C
1	Innut offeet ourrent (e.e. No.	to 4)	V- 5 V	\/ F\/	25°C		0.1		рА
10	Input offset current (see No	te 4)	V _O = 5 V,	$V_{IC} = 5 V$	125°C		1.8	15	nA
	lament hims assument (a.s. Nata	. 4\	V- 5V	V 5.V	25°C		0.7		рА
lΒ	Input bias current (see Note	÷ 4)	V _O = 5 V,	$V_{IC} = 5 V$	125°C		10	35	nA
M	Common-mode input voltag	je range			25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	_			Full range	0 to 8.5			V
					25°C	8	8.7		
∨он	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	−55°C	7.8	8.6		V
					125°C	7.8	8.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
					25°C	25	275		
A_{VD}	Large-signal differential voltage amplification		$V_0 = 1 \text{ V to 6 V},$	$R_L = 100 \text{ k}\Omega$	−55°C	15	420		V/mV
	voltage amplification				125°C	15	190		
					25°C	65	94		
CMRR	Common-mode rejection ra	tio	V _{IC} = V _{ICR} min		−55°C	60	93		dB
					125°C	60	93		
	0 1 11 11				25°C	70	93		
ksvr	Supply-voltage rejection rat (ΔV _{DD} /ΔV _{IO})	10	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	−55°C	60	91		dB
	(4 · DD/4 · IO/				125°C	60	94		
			.,	.,	25°C		570	1200	
I_{DD}	Supply current (four amplific	ers)	V _O = 5 V, No load	$V_{IC} = 5 V$	−55°C		980	2000	μΑ
			110000		125°C		360	960	

[†] Full range is –55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics, V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

	DADAMETED	TEST CONE	NITIONE	TL	.C27M4\	1	UNIT
	PARAMETER	TEST CONL	DITIONS	MIN	TYP	MAX	UNII
V _{IO}	Input offset voltage	$V_O = 1.4 \text{ V},$ $R_S = 50 \Omega,$	$V_{IC} = 0,$ $R_L = 100 \text{ k}\Omega$		1.1	10	mV
α_{VIO}	Temperature coefficient of input offset voltage	T _A = 25°C to 70°C			1.7		μV/°C
IIO	Input offset current (see Note 4)	$V_0 = 2.5 V$,	V _{IC} = 2.5 V		0.1		рА
I _{IB}	Input bias current (see Note 4)	$V_0 = 2.5 V$,	V _{IC} = 2.5 V		0.6		рА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 4	-0.3 to 4.2		V
Vон	High-level output voltage	V _{ID} = 100 mV,	R _L = 100 kΩ	3.2	3.9		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$	I _{OL} = 0		0	50	mV
AVD	Large-signal differential voltage amplification	$V_0 = 0.25 \text{ V to 2 V},$	R _L = 100 kΩ	25	170		V/mV
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR} min		65	91		dB
ksvr	Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	70	93		dB
I _{DD}	Supply current (four amplifiers)	V _O = 2.5 V, No load	V _{IC} = 2.5 V,		420	1120	μΑ

electrical characteristics, V_{DD} = 10 V, T_A = 25°C (unless otherwise noted)

	PARAMETER	TEST CONI	NITIONS	TL	.C27M4\	Y	UNIT
	PARAMETER	TEST CONL	DITIONS	MIN	TYP	MAX	UNIT
V _{IO}	Input offset voltage	$V_{O} = 1.4 \text{ V},$ $R_{S} = 50 \Omega,$	$V_{IC} = 0,$ $R_L = 100 \text{ k}\Omega$		1.1	10	mV
α_{VIO}	Temperature coefficient of input offset voltage	$T_A = 25^{\circ}C \text{ to } 70^{\circ}C$			2.1		μV/°C
IIO	Input offset current (see Note 4)	V _O = 5 V,	V _{IC} = 5 V		0.1		рА
I _{IB}	Input bias current (see Note 4)	$V_0 = 5 V$,	$V_{IC} = 5 V$		0.7		рА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 9	-0.3 to 9.2		V
Vон	High-level output voltage	$V_{ID} = 100 \text{ mV},$	R _L = 100 kΩ	8	8.7		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$	I _{OL} = 0		0	50	mV
A _{VD}	Large-signal differential voltage amplification	$V_0 = 1 \text{ V to 6 V},$	$R_L = 100 \text{ k}\Omega$	25	275		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$		65	94		dB
ksvr	Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	70	93		dB
I _{DD}	Supply current (four amplifiers)	V _O = 5 V, No load	V _{IC} = 5 V,		570	1200	μА

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

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operating characteristics at specified free-air temperature, $V_{DD} = 5 V$

PARAMETER		PARAMETER TE		TEST CONDITIONS		PARAMETER TEST CONDITIONS		TA	TL(C27M4/	AC BC	UNIT
			_		TLC27M4 TLC27M4 TLC27M9 TLC27M9 MIN TYP 0.43 0.46 0.36 0.40 0.43 0.34 32 55 60 50 525 610 400 40° 41°	TYP	MAX					
				25°C		0.43						
			V _{IPP} = 1 V	0°C		0.46		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \				
SR	Clow rote at unity gain	$R_L = 100 \Omega$		70°C		0.36						
J SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs				
		gara i		Ü	Ü		V _{IPP} = 2.5 V	0°C		0.43		
								70°C		0.34		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω	25°C		32		nV/√ Hz				
		,, ,,		25°C		55						
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH},$ $R_L = 100 \text{ k}\Omega,$		0°C		60		kHz				
		TCL = 100 K22,	See rigule r	70°C		50		1				
			_	25°C		525						
B ₁	Unity-gain bandwidth	V _I = 10 mV,	$C_L = 20 \text{ pF},$	0°C		610		kHz				
		See Figure 3	70°C		400							
				25°C		40°						
φm	Phase margin		f = B ₁ , See Figure 3	0°C		41°						
	· ·	OL = 20 pr,	C _L = 20 pF, See Figure 3	70°C		39°						

operating characteristics at specified free-air temperature, V_{DD} = 10 V

PARAMETER		PARAMETER TEST CONDITIONS		TA	TL TL	.C27M4 .C27M4 .C27M4 .C27M9	AC BC	UNIT	
			1	25°C	IVIIIV	0.62	IVIAA		
		V _{IPP} = 1 V		0°C		0.67		1	
	$R_L = 100 \Omega$	VIPP - I V	70°C		0.51		1		
SR	Slew rate at unity gain	C _L = 20 pF,		25°C		0.56		V/μs	
		See Figure 1	See Figure 1	V _{IPP} = 5.5 V	0°C		0.61		
			"	70°C		0.46		1	
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz	
	Maximum output-swing bandwidth Vo = Vol			25°C		35			
ВОМ		VO = VOH,	C _L = 20 pF,	0°C		40		kHz	
		$R_L = 100 \text{ k}\Omega,$	See Figure 1	70°C		30		1	
				25°C		635			
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	0°C		710		kHz	
		See Figure 3		70°C		510		1	
				25°C		43°			
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C		44°		1	
	S	OL = 20 pr,	oce i iguie o	70°C		42°			

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operating characteristics at specified free-air temperature, $V_{DD} = 5 V$

	PARAMETER TEST CONDITIONS		TA	TLC27M4I TLC27M4AI TLC27M4BI TLC27M9I		AI BI	UNIT	
					MIN	TYP	MAX	
				25°C		0.43		
			V _{IPP} = 1 V	−40°C		0.51		
SR	Claw rate at unity gain	$R_L = 100 \Omega$		85°C		0.35		\//ua
J SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs
	V _{IPP} = 2.5 V	−40°C		0.48				
						0.32		
Vn	Equivalent input noise voltage	f = 1 kHz _, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		55		
ВОМ	Maximum output-swing bandwidth	Maximum output-swing bandwidth $V_O = V_{OH}$, $C_L = 20 \text{pF}$, $R_L = 100 \text{k}\Omega$, See Figure 1 -40°C		−40°C		75		kHz
				45				
				25°C		525		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 \text{ pF},$	−40°C		770		kHz
		occ rigare s		85°C		370		
				25°C		40°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	−40°C		43°		
		OL = 20 pr ,	occ i iguie o	85°C		38°		

operating characteristics at specified free-air temperature, V_{DD} = 10 V

PARAMETER		PARAMETER TEST CONDITIONS		TA	TL TL TL	.C27M4I .C27M4I .C27M4I .C27M9I	AI BI	UNIT
					MIN	TYP	MAX	
			25°C		0.62			
		V _{IPP} = 1 V	−40°C		0.77			
SR	Clause rate at units agin	$R_L = 100 \Omega$		85°C		0.47		1//
SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μS
		3	V _{IPP} = 5.5 V	-40°C		0.70		V/μs nV/√ Hz
			l" F			0.44		1
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
	Maximum output-swing bandwidth			25°C		35		
ВОМ		$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,	C _L = 20 pF, See Figure 1	−40°C		45		kHz
			occ i iguic i	85°C		25		1
				25°C		635		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	−40°C		880		kHz
		occ rigule 3		85°C		480		1
				25°C		43°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	−40°C		46°		1
	-	о_ = 20 рг,	Occ i iguie 3	85°C		41°		

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operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CC	ONDITIONS	TA		-		UNIT
					0.4 0.5 0.2 0.4 0.5 0.2 3. 5. 8 4 52: 85 33 40	TYP	MAX	
				25°C		0.43		
			V _{IPP} = 1 V	−55°C		0.54		
SR	Slow rate at unity gain	$R_L = 100 \Omega$		125°C		0.29		\//uo
J SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs
			V _{IPP} = 2.5 V	−55°C		0.50		
					125°C		0.28	
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		55		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_I = 100 \text{ k}\Omega$,		−55°C		80		kHz
			Occ rigure r	125°C		40		
				25°C		525		
В ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF,$	−55°C	850	kHz		
		Occ riguic 3		125°C		330		
						40°		
φm	Phase margin	$\label{eq:V_l} \begin{array}{ll} V_l = 10 \text{ mV}, & f = B_1, \\ C_L = 20 \text{ pF}, & \text{See Figure 3} \end{array}$	−55°C		44°			
	-	о_ = 20 рг,	Occ i iguie 3	125°C		36°		

operating characteristics at specified free-air temperature, V_{DD} = 10 V

PARAMETER		TEST (CONDITIONS	TA		C27M4I		UNIT
					MIN	TYP	MAX	
				25°C		0.62		
			V _{IPP} = 1 V	−55°C		0.81		
ep.	Slow rate at unity gain	$R_L = 100 \Omega$		125°C		0.38		V/μs
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		ν/μδ
			V _{IPP} = 5.5 V	−55°C		0.73		
		1	125°C		0.35		1	
٧n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		35		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,	C _L = 20 pF, See Figure 1	−55°C		50		kHz
			occ i iguic i	125°C		20		
				25°C		635		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 \text{ pF},$	−55°C		960		kHz
		See Figure 3	oco i iguito o	125°C		440		
	-			25°C		43°		
φm	Phase margin	$V_{l} = 10 \text{ mV},$		−55°C		47°		
		C _L = 20 pF, See Figure 3		125°C		39°		

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operating characteristics, V_{DD} = 5 V, T_A = 25°C

PARAMETER		TEST CO.	TEST CONDITIONS		C27M4	1	UNIT
	PARAMETER	lE31 COI	NDITIONS	MIN TYP MAX		CIVIT	
SR	Slew rate at unity gain	$R_L = 100 \text{ k}\Omega$, $V_{IPP} = 1 \text{ V}$			0.43		\//uo
SK	Siew rate at unity gain	C _L = 20 pF, See Figure 1	V _{IPP} = 2.5 V		0.40		V/μs
Vn	Equivalent input noise voltage	f = 1 kHz _, See Figure 2	$R_S = 20 \Omega$,		32		nV/√ Hz
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,	C _L = 20 pF, See Figure 1		55		kHz
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,		525		kHz
φm	Phase margin	$V_I = 10 \text{ mV},$ $C_L = 20 \text{ pF},$	f = B ₁ , See Figure 3		40°	·	

operating characteristics, V_{DD} = 10 V, T_A = 25°C

	PARAMETER	TEST CO	TEST CONDITIONS		TLC27M4Y		
	PARAMETER	1231 00	NUTTIONS	MIN TYP MAX		UNIT	
SR	Claus rate at units agin	$R_L = 100 \text{ k}\Omega,$ $V_{IPP} = 1 \text{ V}$			0.62		V/µs
SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1	V _{IPP} = 5.5 V		0.56		ν/μ5
V _n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,		32		nV/√ Hz
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,	C _L = 20 pF, See Figure 1		35		kHz
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,		635		kHz
φ _m	Phase margin	$V_I = 10 \text{ mV},$ $C_L = 20 \text{ pF},$	f = B ₁ , See Figure 3		43°	·	

PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC27M4 and TLC27M9 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

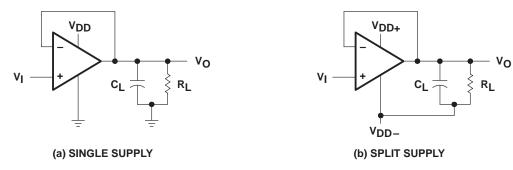


Figure 1. Unity-Gain Amplifier

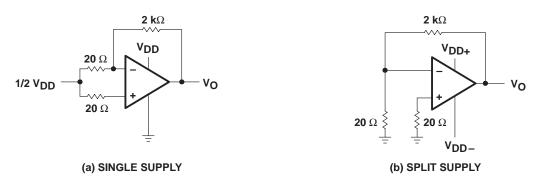


Figure 2. Noise-Test Circuit

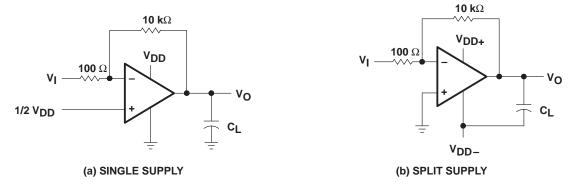


Figure 3. Gain-of-100 Inverting Amplifier

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PARAMETER MEASUREMENT INFORMATION

input bias current

Because of the high input impedance of the TLC27M4 and TLC27M9 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution—many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current; the voltage drop across the series resistor is measured and the bias current is calculated. This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

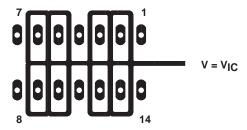


Figure 4. Isolation Metal Around Device Inputs (J and N packages)

low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the *Typical Characteristics* of this data sheet.

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PARAMETER MEASUREMENT INFORMATION

input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.

full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output, while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.



Figure 5. Full-Power-Response Output Signal

test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.

Table of Graphs

			FIGURE
VIO	Input offset voltage	Distribution	6, 7
ανιο	Temperature coefficient of input offset voltage	Distribution	8, 9
Vон	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
VOL	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
I _{IB}	Input bias current	vs Free-air temperature	22
lio	Input offset current	vs Free-air temperature	22
VIC	Common-mode input voltage	vs Supply voltage	23
I _{DD}	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
VO(PP)	Maximum peak-to-peak output voltage	vs Frequency	29
B ₁	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
	Phase shift	vs Frequency	32, 33
фm	Phase margin	vs Supply voltage vs Free-air temperature vs Load capacitance	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37

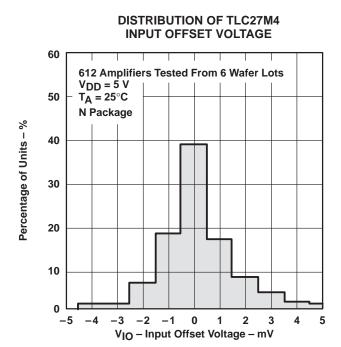
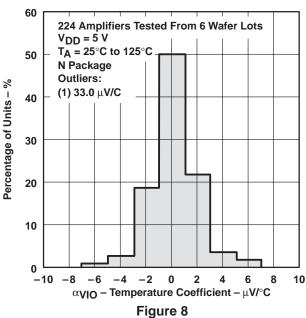


Figure 6

DISTRIBUTION OF TLC27M4 AND TLC27M9 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT



DISTRIBUTION OF TLC27M4 INPUT OFFSET VOLTAGE

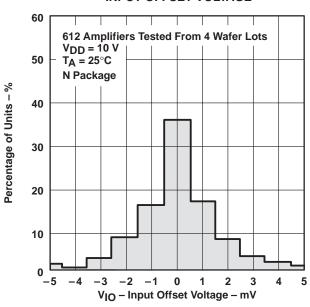
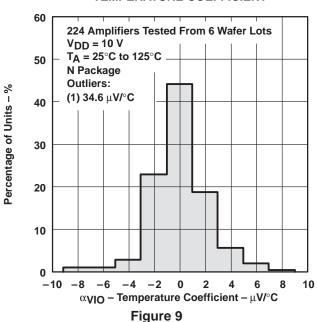
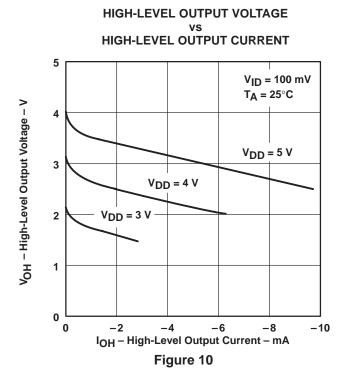


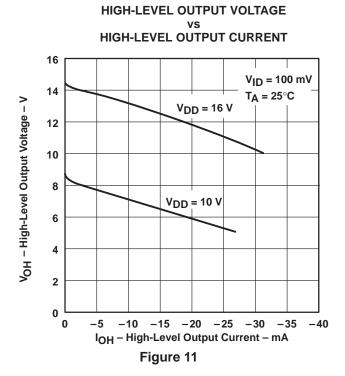
Figure 7

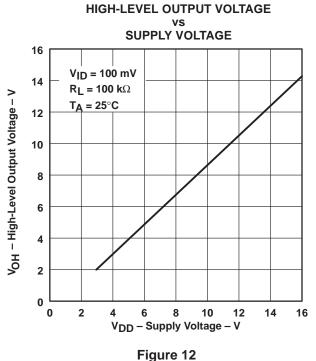
DISTRIBUTION OF TLC27M4 AND TLC27M9 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

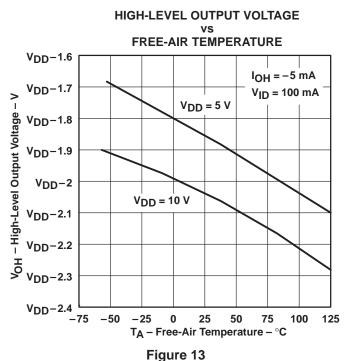


TYPICAL CHARACTERISTICS[†]



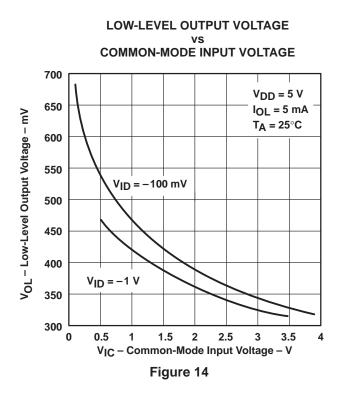


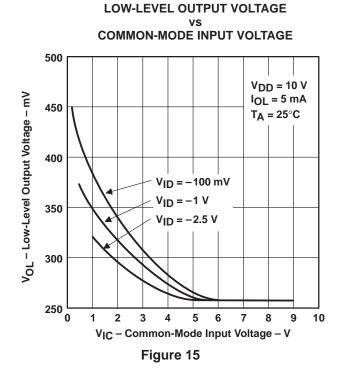


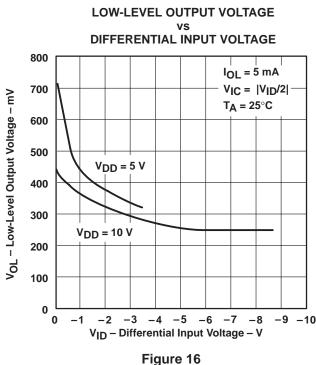


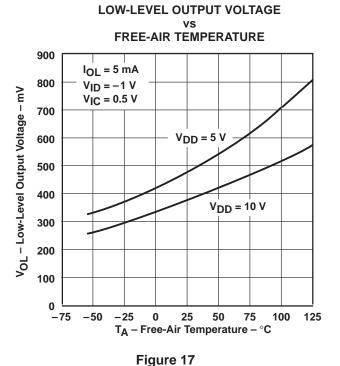
[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





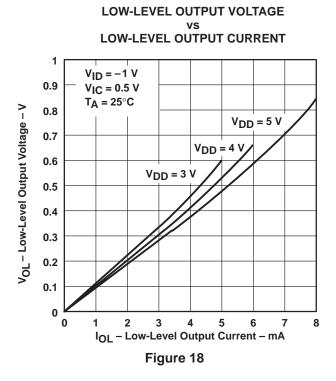


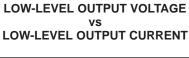


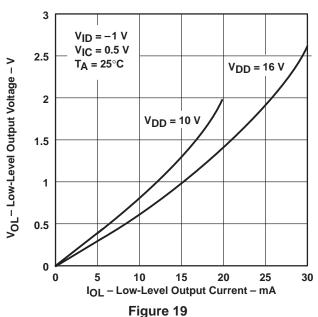


† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

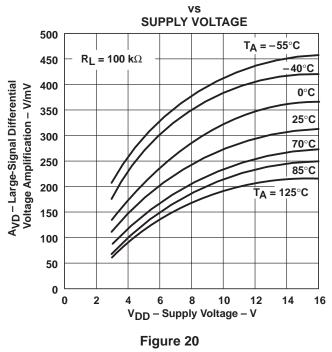
TYPICAL CHARACTERISTICS[†]







LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION



LARGE-SIGNAL **DIFFERENTIAL VOLTAGE AMPLIFICATION**

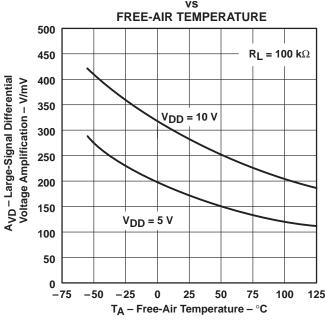
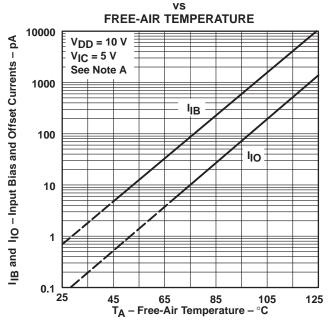


Figure 21

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

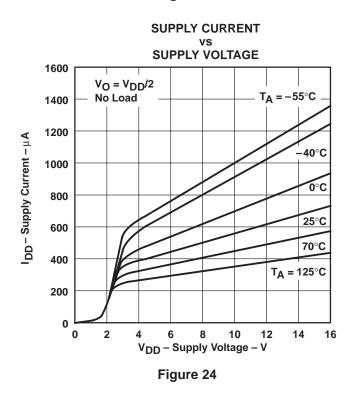


INPUT BIAS CURRENT AND INPUT OFFSET CURRENT



NOTE A: The typical values of input bias current and input offset current below 5 pA were determined mathematically.

Figure 22



COMMON-MODE INPUT VOLTAGE POSITIVE LIMIT

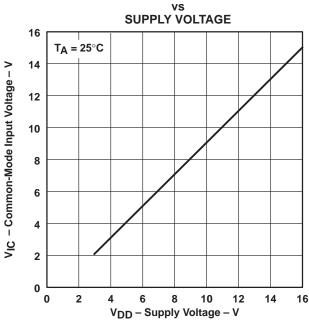
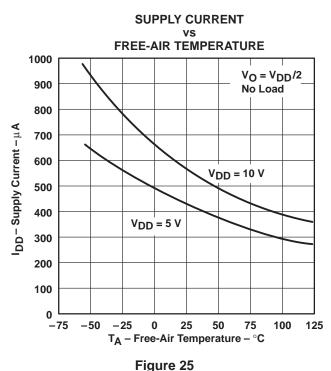
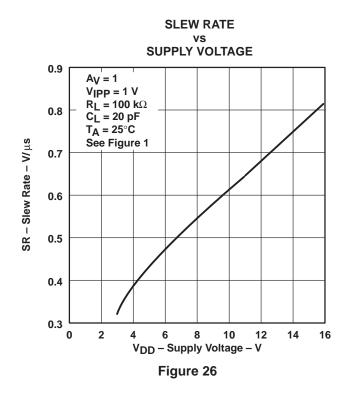


Figure 23



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





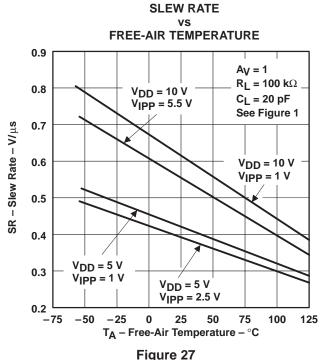
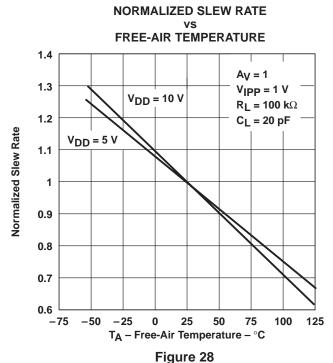
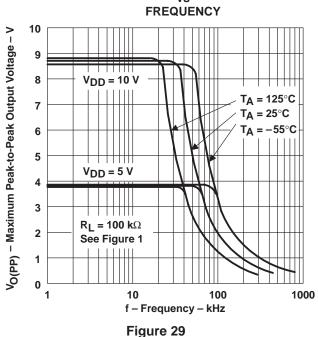


Figure 2

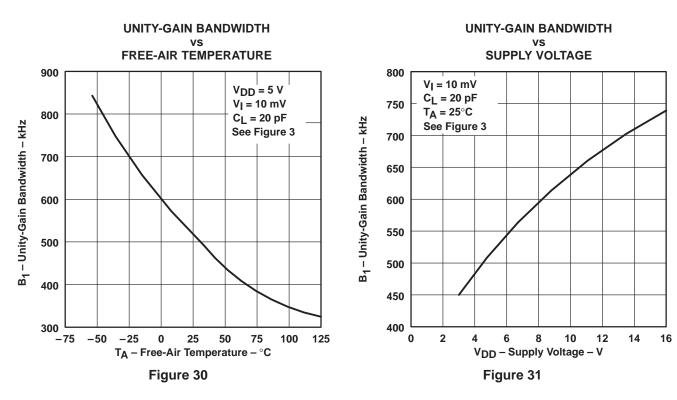


MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE vs

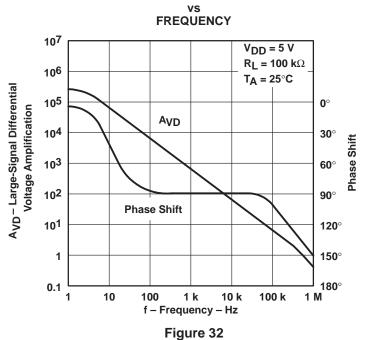


[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS[†]

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

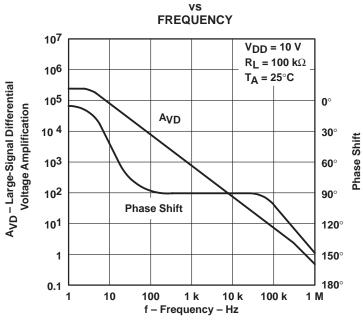
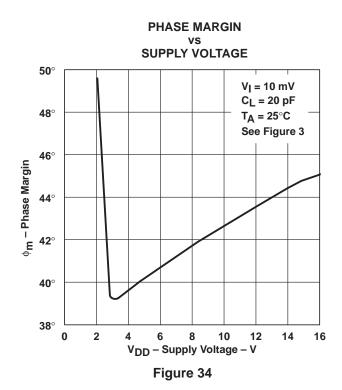
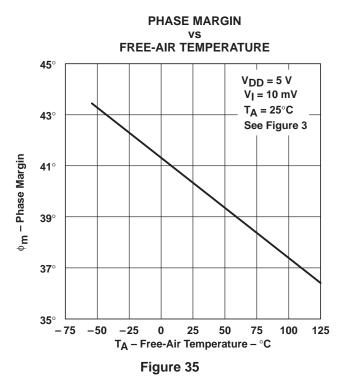


Figure 33





[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



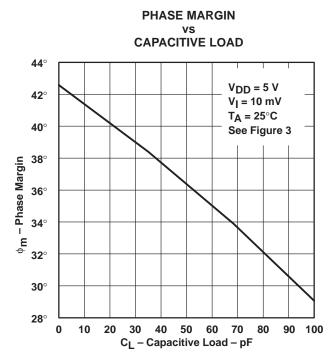


Figure 36

EQUIVALENT INPUT NOISE VOLTAGE VS FREQUENCY

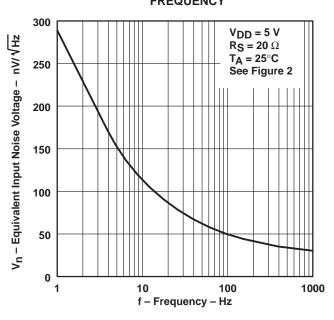


Figure 37

single-supply operation

While the TLC27M4 and TLC27M9 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27M4 and TLC27M9 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27M4 and TLC27M9 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

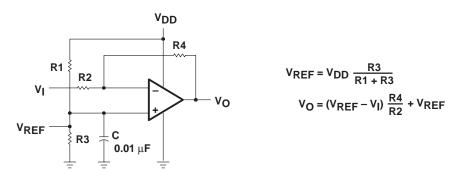


Figure 38. Inverting Amplifier With Voltage Reference

single-supply operation (continued)

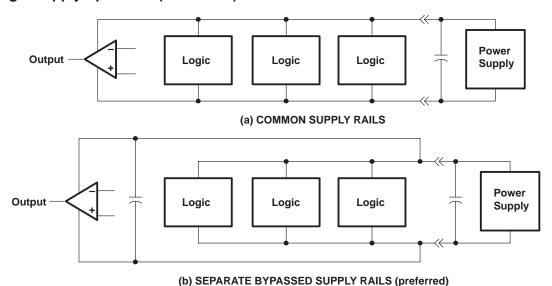


Figure 39. Common Versus Separate Supply Rails

input characteristics

The TLC27M4 and TLC27M9 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at $V_{DD} - 1$ V at $T_A = 25$ °C and at $V_{DD} - 1.5$ V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC27M4 and TLC27M9 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1 μ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27M4 and TLC27M9 are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the *Parameter Measurement Information* section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

Unused amplifiers should be connected as unity-gain followers to avoid possible oscillation.

noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27M4 and TLC27M9 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than $50\,\mathrm{k}\Omega$, since bipolar devices exhibit greater noise currents.

noise performance (continued)

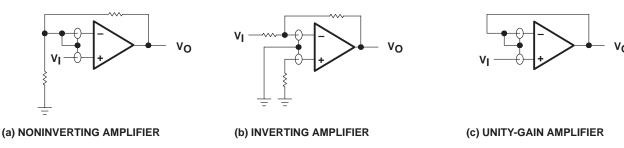


Figure 40. Guard-Ring Schemes

output characteristics

The output stage of the TLC27M4 and TLC27M9 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

All operating characteristics of the TLC27M4 and TLC27M9 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.

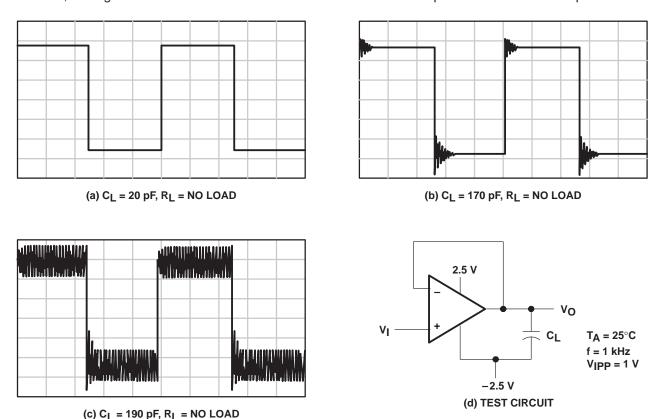
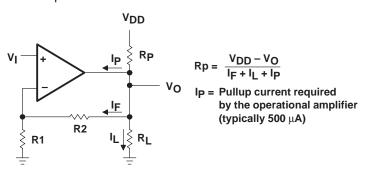


Figure 41. Effect of Capacitive Loads and Test Circuit



output characteristics (continued)

Although the TLC27M4 and TLC27M9 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (R_P) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately $60~\Omega$ and $180~\Omega$, depending on how hard the operational amplifier input is driven. With very low values of R_P, a voltage offset from 0 V at the output occurs. Second, pullup resistor R_P acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.



v_o

Figure 42. Resistive Pullup to Increase V_{OH}

Figure 43. Compensation for Input Capacitance

feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

electrostatic discharge protection

The TLC27M4 and TLC27M9 incorporate an internal electrostatic discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices, as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature-dependent and have the characteristics of a reverse-biased diode.

latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27M4 and TLC27M9 inputs and outputs were designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

latch-up (continued)

The current path established if latch-up occurs is usually between the positive supply rail and ground; it can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

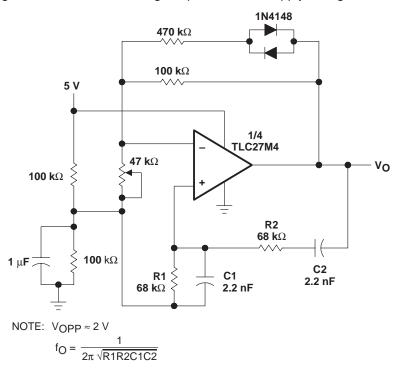


Figure 44. Wien Oscillator

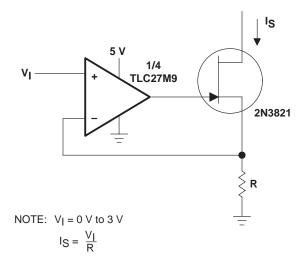
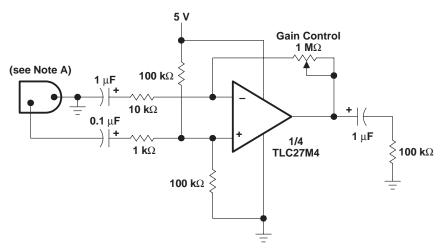


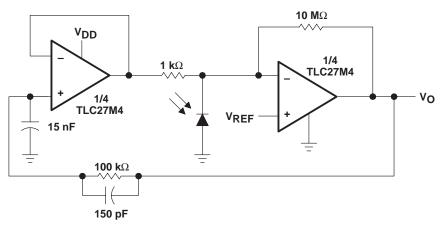
Figure 45. Precision Low-Current Sink





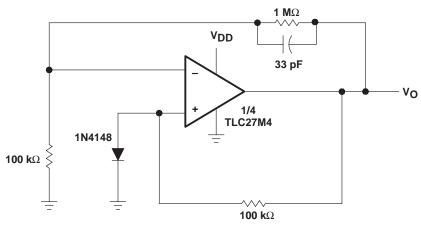
NOTE A: Low to medium impedance dynamic mike

Figure 46. Microphone Preamplifier



NOTE: $V_{DD} = 4 \text{ V to } 15 \text{ V}$ $V_{REF} = 0 \text{ V to } V_{DD} - 2 \text{ V}$

Figure 47. Photo-Diode Amplifier With Ambient Light Rejection



NOTE: $V_{DD} = 8 \text{ V to } 16 \text{ V}$ $V_{O} = 5 \text{ V}$, 10 mA

Figure 48. Low-Power Voltage Regulator

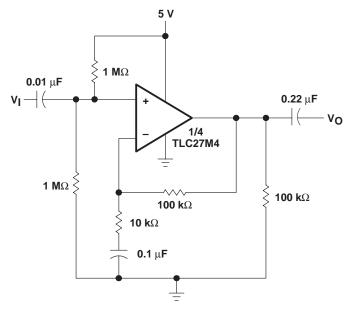


Figure 49. Single-Rail AC Amplifier

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